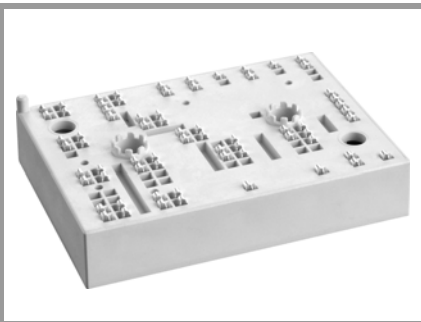


# SKiiP 39AC12T7V1



MiniSKiiP® 3

## Sixpack

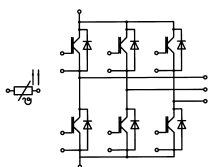
### SKiiP 39AC12T7V1

#### Features\*

- 1200V Generation 7 IGBTs (T7)
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

#### Remarks

- Max. case temperature limited to  $T_C=125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^\circ\text{C}$ )
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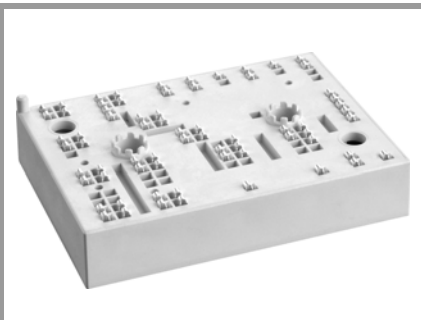


AC

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
<b>Inverter - IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$		1200	V
$I_C$	$\lambda_{paste}=0.8 \text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	135	A
		$T_j = 175^\circ\text{C}$	109	A
$I_C$	$\lambda_{paste}=2.5 \text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	158	A
		$T_j = 175^\circ\text{C}$	128	A
$I_{Chom}$			150	A
$I_{CRM}$			300	A
$V_{GES}$			-20 ... 20	V
$t_{psc}$	$V_{CC} = 800 \text{ V}$ $V_{GE} \leq 15 \text{ V}$ $V_{CES} \leq 1200 \text{ V}$	$T_j = 175^\circ\text{C}$	7	$\mu\text{s}$
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Inverse - Diode</b>				
$I_F$	$\lambda_{paste}=0.8 \text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	103	A
		$T_j = 175^\circ\text{C}$	82	A
$I_F$	$\lambda_{paste}=2.5 \text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	128	A
		$T_j = 175^\circ\text{C}$	102	A
$I_{FRM}$			300	A
$I_{FSM}$	$t_p = 10 \text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$		900	A
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}, 20 \text{ A per spring}$		160	A
$T_{stg}$	module without TIM		-40 ... 125	$^\circ\text{C}$
$V_{isol}$	AC sinus 50 Hz, $t = 1 \text{ min}$		2500	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverter - IGBT</b>						
$V_{CE(sat)}$	$I_C = 150 \text{ A}$ $V_{GE} = 15 \text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.55	1.70		V
		$T_j = 150^\circ\text{C}$	1.72	1.96		V
		$T_j = 175^\circ\text{C}$	1.75	2.01		V
$V_{CE0}$	chipelevel	$T_j = 25^\circ\text{C}$	0.90	1.00		V
		$T_j = 150^\circ\text{C}$	0.75	0.83		V
		$T_j = 175^\circ\text{C}$	0.72	0.80		V
$r_{CE}$	$V_{GE} = 15 \text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	4.3	4.7		$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	6.5	7.5		$\text{m}\Omega$
		$T_j = 175^\circ\text{C}$	6.9	8.1		$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3.4 \text{ mA}$		5.15	5.8	6.45	V
$I_{CES}$	$V_{GE} = 0 \text{ V}, V_{CE} = 1200 \text{ V}, T_j = 25^\circ\text{C}$				1.5	$\text{mA}$
$C_{ies}$				30.20		nF
$C_{oes}$	$V_{CE} = 25 \text{ V}$			0.39		nF
$C_{res}$	$V_{GE} = 0 \text{ V}$			1.08		nF
$Q_G$	$V_{GE} = -8 \text{ V} \dots +15 \text{ V}$			2100		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$			1.0		$\Omega$

# SKiiP 39AC12T7V1



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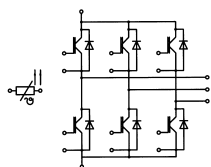
## SKiiP 39AC12T7V1

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- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

### Remarks

- Max. case temperature limited to  $T_C=125^\circ\text{C}$
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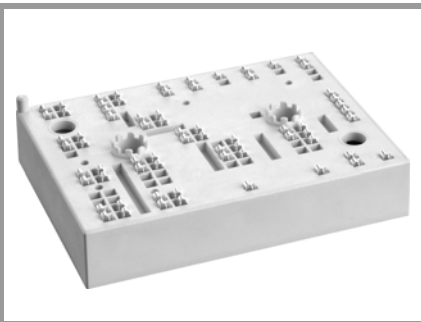


AC

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>Inverter - IGBT</b>					
$t_{d(on)}$		$T_j = 25^\circ\text{C}$	173		ns
$t_{d(on)}$		$T_j = 150^\circ\text{C}$	181		ns
$t_{d(on)}$		$T_j = 175^\circ\text{C}$	179		ns
$t_r$		$T_j = 25^\circ\text{C}$	32		ns
$t_r$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	37		ns
$t_r$	$I_C = 150\text{ A}$	$T_j = 175^\circ\text{C}$	39		ns
$E_{on}$	$R_{G, on} = 1.1\ \Omega$	$T_j = 25^\circ\text{C}$	6.9		mJ
$E_{on}$	$R_{G, off} = 1.1\ \Omega$	$T_j = 150^\circ\text{C}$	12		mJ
$E_{on}$	$V_{GE} = +15/-15\text{ V}$	$T_j = 175^\circ\text{C}$	13		mJ
$t_{d(off)}$		$T_j = 25^\circ\text{C}$	347		ns
$t_{d(off)}$	@ $T_j = 150^\circ\text{C}$ :	$T_j = 150^\circ\text{C}$	437		ns
$t_{d(off)}$	$di/dt_{on} = 3970\text{ A}/\mu\text{s}$	$T_j = 175^\circ\text{C}$	462		ns
$t_f$	$di/dt_{off} = 1530\text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	67		ns
$t_f$	$dv/dt = 3730\text{ V}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	103		ns
$t_f$		$T_j = 175^\circ\text{C}$	130		ns
$E_{off}$		$T_j = 25^\circ\text{C}$	10		mJ
$E_{off}$		$T_j = 150^\circ\text{C}$	17		mJ
$E_{off}$		$T_j = 175^\circ\text{C}$	18		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8\text{ W}/(\text{mK})$		0.41		K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5\text{ W}/(\text{mK})$		0.32		K/W

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>Inverse - Diode</b>					
$V_F = V_{EC}$	$I_F = 150\text{ A}$	$T_j = 25^\circ\text{C}$	2.14	2.46	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$	2.07	2.38	V
	chipllevel	$T_j = 175^\circ\text{C}$	1.93	2.24	V
$V_{F0}$		$T_j = 25^\circ\text{C}$	1.30	1.50	V
	chipllevel	$T_j = 150^\circ\text{C}$	0.90	1.10	V
		$T_j = 175^\circ\text{C}$	0.82	0.98	V
$r_F$		$T_j = 25^\circ\text{C}$	5.6	6.4	m $\Omega$
	chipllevel	$T_j = 150^\circ\text{C}$	7.8	8.5	m $\Omega$
		$T_j = 175^\circ\text{C}$	7.4	8.4	m $\Omega$
$I_{RRM}$		$T_j = 25^\circ\text{C}$	107		A
		$T_j = 150^\circ\text{C}$	145		A
	$I_F = 150\text{ A}$	$T_j = 175^\circ\text{C}$	175		A
$Q_{rr}$	$V_{GE} = +15/-15\text{ V}$	$T_j = 25^\circ\text{C}$	7.4		$\mu\text{C}$
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	24		$\mu\text{C}$
	@ $T_j = 150^\circ\text{C}$ :	$T_j = 175^\circ\text{C}$	24.5		$\mu\text{C}$
$E_{rr}$	$di/dt_{off} = 3910\text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	2.6		mJ
		$T_j = 150^\circ\text{C}$	8.6		mJ
		$T_j = 175^\circ\text{C}$	11		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8\text{ W}/(\text{mK})$		0.55		K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=2.5\text{ W}/(\text{mK})$		0.4		K/W
<b>Module</b>					
$L_{CE}$			-		nH
$M_s$	to heat sink	2		2.5	Nm
$w$			82		g

# SKiiP 39AC12T7V1



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### SKiiP 39AC12T7V1

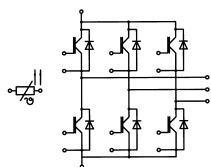
#### Features\*

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Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>Temperature Sensor</b>					
$R_{100}$	$T_r=100^{\circ}\text{C}$ ( $R_{25}=1000\Omega$ )		$1670 \pm 3\%$		$\Omega$
$R(T)$	$R(T)=1000\Omega[1+A(T-25^{\circ}\text{C})+B(T-25^{\circ}\text{C})^2]$ $A = 7.635 \cdot 10^{-3} \text{ } ^{\circ}\text{C}^{-1}$ , $B = 1.731 \cdot 10^{-5} \text{ } ^{\circ}\text{C}^{-2}$				



AC

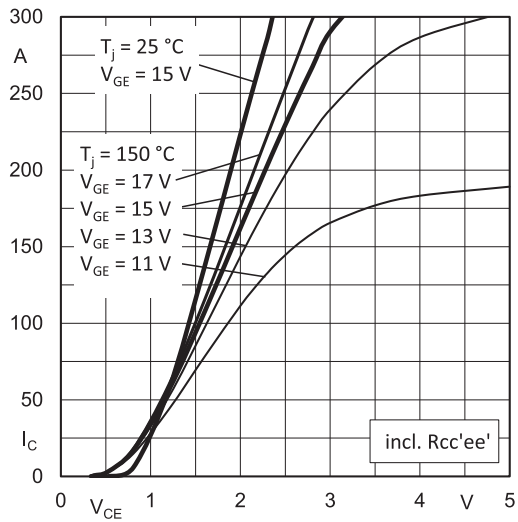


Fig. 1: Typ. output characteristic, inclusive  $R_{CC'+EE'}$

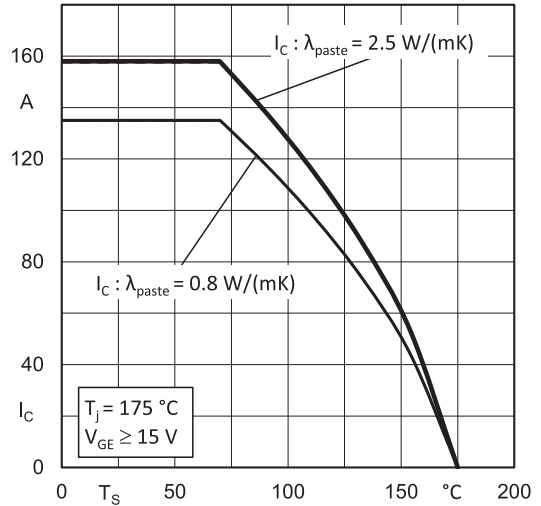


Fig. 2: Rated current vs. temperature  $I_C = f(T_S)$

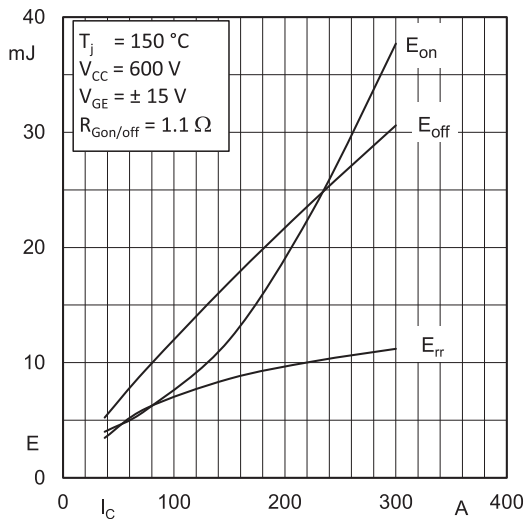


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

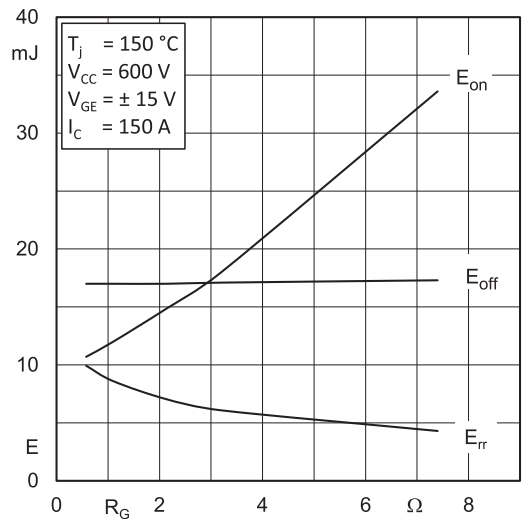


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

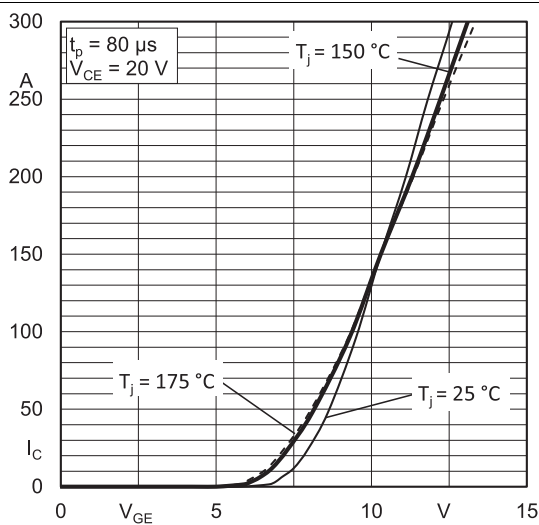


Fig. 5: Typ. transfer characteristic

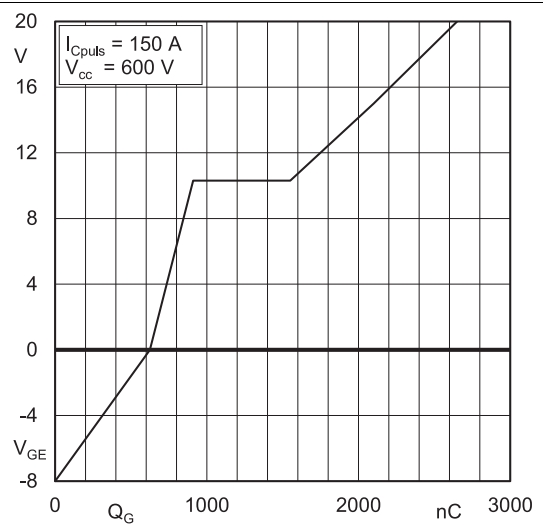


Fig. 6: Typ. gate charge characteristic

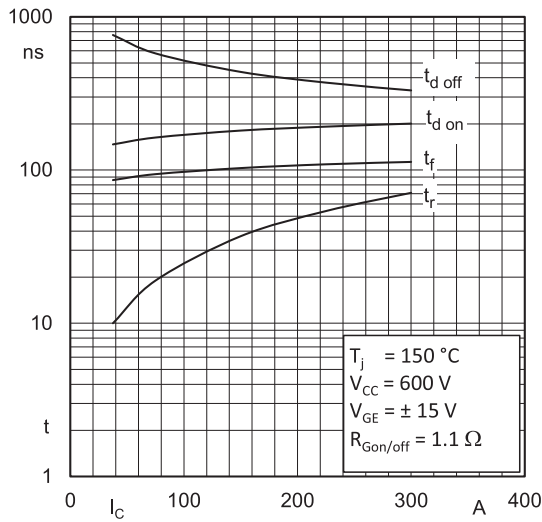


Fig. 7: Typ. switching times vs.  $I_C$

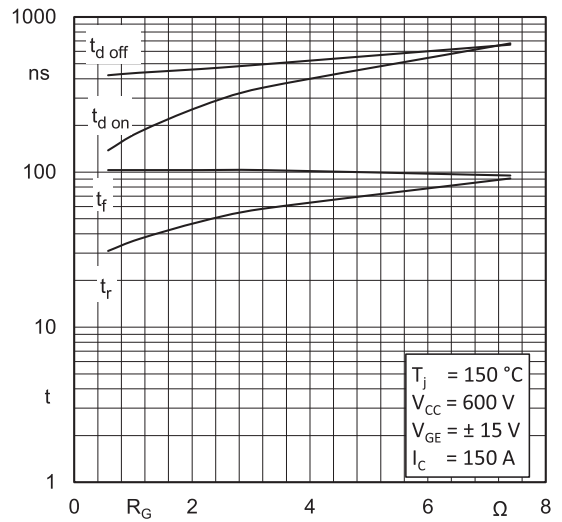


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

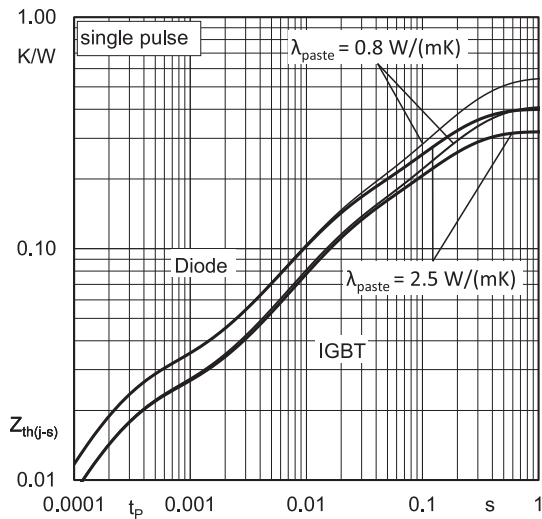


Fig. 9: Transient thermal impedance of IGBT and Diode

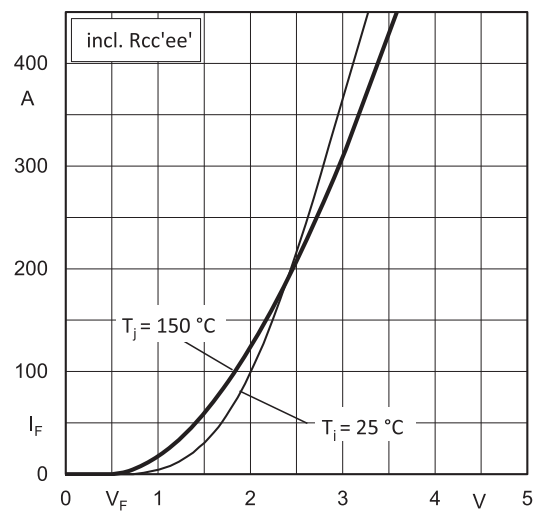


Fig. 10: Typ. CAL diode forward charact., incl.  $R_{CC+EE}$

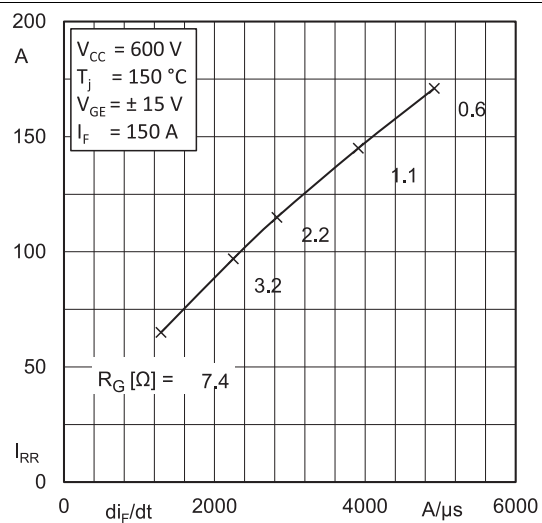


Fig. 11: Typ. CAL diode peak reverse recovery current

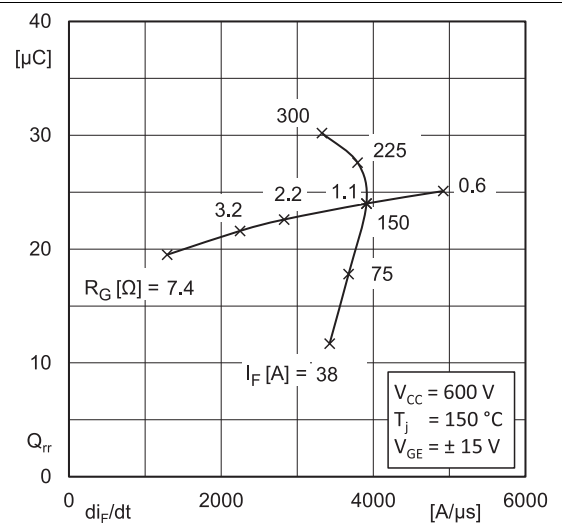
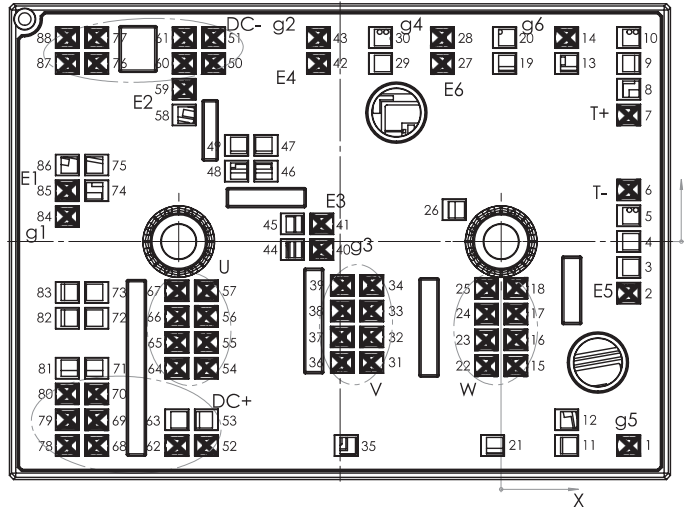


Fig. 12: Typ. CAL diode recovery charge

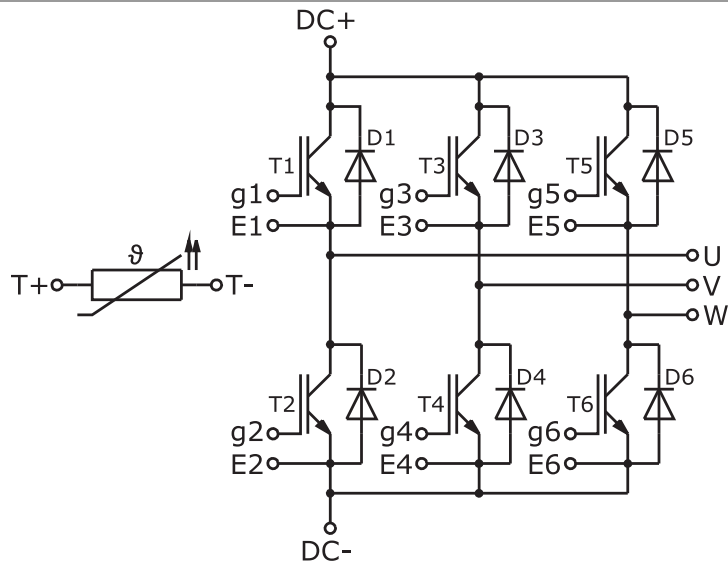
# SKiiP 39AC12T7V1

Pin out											
Pin	X	Y	Function	Pin	X	Y	Function	Pin	X	Y	Function
1	15,83	-25,3	g5	31	-16,05	-15,02	V	61	-39,33	25,3	DC-
2	15,83	-6,4	E5	32	-16,05	-11,82	V	62	-40,23	-25,3	DC+
3				33	-16,05	-8,62	V	63			
4				34	-16,05	-5,42	V	64	-40,23	-15,7	U
5				35				65	-40,23	-12,5	U
6	15,83	6,4	T-	36	-19,7	-15,02	V	66	-40,23	-9,3	U
7	15,83	15,7	T+	37	-19,7	-11,82	V	67	-40,23	-6,1	U
8				38	-19,7	-8,62	V	68	-50,18	-25,3	DC+
9				39	-19,7	-5,42	V	69	-50,18	-22,1	DC+
10				40	-22,26	-1	g3	70	-50,18	-15,7	DC+
11				41	-22,26	2	E3	71			
12				42	-22,68	22,1	E4	72			
13				43	-22,68	25,3	g2	73			
14	8,13	25,3	g6	44				74			
15	1,83	-15,39	W	45				75			
16	1,83	-12,19	W	46				76	-50,18	22,1	DC-
17	1,83	-8,99	W	47				77	-50,18	25,3	DC-
18	1,83	-5,79	W	48				78	-53,83	-25,3	DC+
19				49				79	-53,83	-22,1	DC+
20				50	-35,68	22,1	DC-	80	-53,83	-15,7	DC+
21				51	-35,68	25,3	DC-	81			
22	-1,83	-15,39	W	52	-36,58	-25,3	DC+	82			
23	-1,83	-12,19	W	53				83			
24	-1,83	-8,99	W	54	-36,58	-15,7	U	84	-53,83	3,1	g1
25	-1,83	-5,79	W	55	-36,58	-12,5	U	85	-53,83	6,3	E1
26				56	-36,58	-9,3	U	86			
27	-7,28	22,1	E6	57	-36,58	-6,1	U	87	-53,83	22,1	DC-
28	-7,28	25,3	g4	58				88	-53,83	25,3	DC-
29				59	-39,33	18,9	E2				
30				60	-39,33	22,1	DC-				

all values in mm



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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